



DC to 3500 MHz, CASCADABLE SiGe HBT MMIC AMPLIFIER

Package: SOT-363

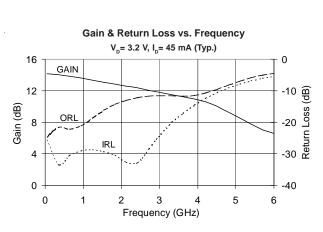




Product Description

The SGA4263Z is a high performance SiGe HBT MMIC Amplifier. A Darlington configuration featuring one-micron emitters provides high F_T and excellent thermal performance. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products. Only two DC-blocking capacitors, a bias resistor, and an optional RF choke are required for operation.





Features

- Broadband Operation: DC to 3500MHz
- Cascadable 50Ω
- Operates from Single Supply
- Low Thermal Resistance Package

Applications

- PA Driver Amplifier
- Cellular, PCS, GSM, UMTS
- IF Amplifier
- Wireless Data, Satellite

Parameter	Specification			Unit	Condition		
Farameter	Min.	Тур.	Max.	UIIIL	Condition		
Small Signal Gain	12.5	14.0	15.5	dB	850MHz		
		12.7		dB	1950MHz		
		12.4		dB	2400MHz		
Output Power at 1dB Compression		14.2		dBm	850MHz		
		12.5		dBm	1950MHz		
Output Third Intercept Point		29.3		dBm	850MHz		
		25.7		dBm	1950MHz		
Bandwidth Determined by Return Loss		3500		MHz	>10dB		
Input Return Loss		31.3		dB	1950MHz		
Output Return Loss		13.8		dB	1950MHz		
Noise Figure		3.7		dB	1950MHz		
Device Operating Voltage	2.9	3.2	3.5	V			
Device Operating Current	41	45	49	mA			
Thermal Resistance (Junction - Lead)		255		°C/W			

Test Conditions: $V_S = 8V$, $I_D = 45$ mA Typ., OIP_3 Tone Spacing = 1 MHz, P_{OUT} per tone = -5 dBm, $R_{BIAS} = 110\Omega$, $T_L = 25$ °C, $Z_S = Z_L = 50\Omega$



Absolute Maximum Ratings

Parameter	Rating	Unit
Max Device Current (I _D)	90	mA
Max Device Voltage (V _D)	5	V
Max RF Input Power	+18	dBm
Max Junction Temp (T _J)	+150	°C
Operating Temp Range (T _L)	-40 to +85	°C
Max Storage Temp	+150	°C

Operation of this device beyond any one of these limits may cause permanent damage. For reliable continuous operation, the device voltage and current must not exceed the maximum operating values specified in the table on page one. Bias Conditions should also satisfy the following expression: $I_DV_D < (T_J - T_L) / \, R_{TH}, \, j \text{-} I$



Caution! ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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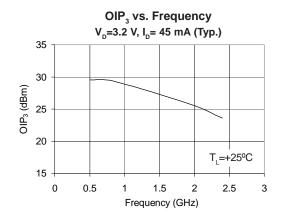


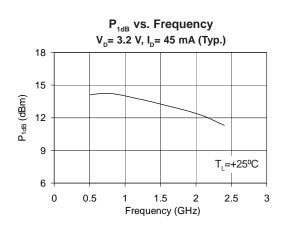
RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in solder.

Typical Performance with 2.45 GHz Application Circuit

Parameter	Unit	100	500	850	1950	2400	3500
		MHz	MHz	MHz	MHz	MHz	MHz
Small Signal Gain	dB	14.1	13.9	14.0	12.7	12.4	11.3
Output Third Order Intercept Point	dBm		29.5	29.3	25.7	23.6	
Output Power at 1dB Compression	dBm		14.1	14.2	12.5	11.3	
Input Return Loss	dB	27.5	31.8	29.4	31.3	33.1	18.3
Output Return Loss	dB	23.4	22.0	21.7	13.8	12.2	11.7
Reverse Isolation	dB	17.7	18.3	18.5	19.0	19.0	18.2
Noise Figure	dB		3.6	3.4	3.7	4.3	

Test Conditions: $V_S = 8V$, $I_D = 45 \text{ mA}$ Typ., OIP_3 Tone Spacing = 1MHz, P_{OLIT} per tone = -10 dBm, $R_{BIAS} = 100 \Omega$, $T_L = 25 \,^{\circ}C$, $Z_S = Z_L = 50 \Omega$



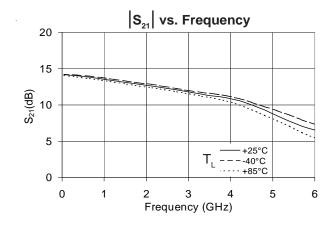


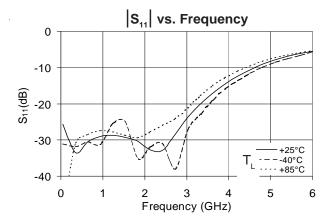
Noise Figure vs. Frequency V_D= 3.2 V, I_D= 45 mA (Typ.) (ap) apple 3 T_L=+25°C 0 0 0.5 1 1.5 2 2.5 3

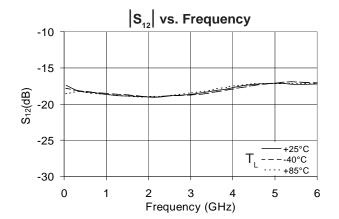
Frequency (GHz)

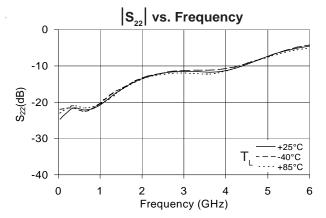


Typical RF Performance Over Temperature (Bias: V_D = 3.2 V, I_D = 45 mA (Typ.))





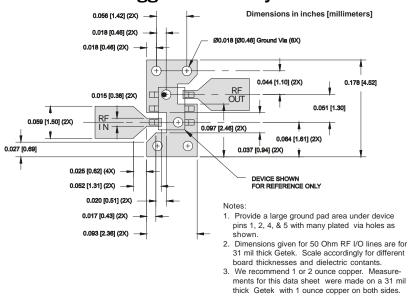






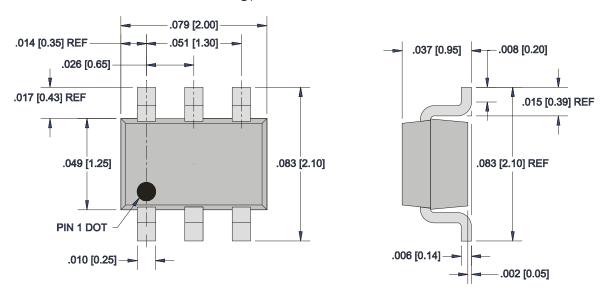
Pin	Function	Description
3	RF IN	RF input pin. This pin requires the use of an external DC-blocking capacitor chosen for the frequency of operation.
1, 2, 4, 5	GND	Connection to ground. For optimum RF performance, use via holes as close to ground leads as possible to reduce lead inductance as close to ground leads as possible.
6	RF OUT/BIAS	RF output and bias pin. DC voltage is present on this pin, therefor a DC-blocking capacitor is necessary for proper operation.

Suggested Pad Layout



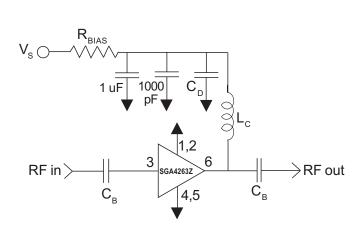
Package Drawing

Dimensions in inches (millimeters)
Refer to drawing posted at www.rfmd.com for tolerances.





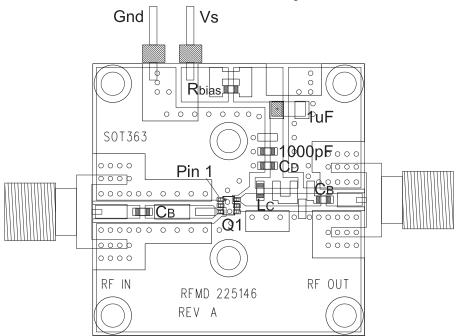
Application Schematic



Reference	Frequency (Mhz)						
Designator	500	850	1950	2400	3500		
C _B	220 pF	100 pF	68 pF	56 pF	39 pF		
C _D	100 pF	68 pF	22 pF	22 pF	15 pF		
L _c	68 nH	33 nH	22 nH	18 nH	15 nH		

Recommended Bias Resistor Values for I_D =45mA R_{BIAS} =(V_S - V_D) / I_D					
Supply Voltage(V _s)	6 V	8 V	10 V	12 V	
R_{BIAS} 62 Ω 110 Ω 150 Ω 200 Ω					
Note: R _{BIAS} provides DC bias stability over temperature.					

Evaluation Board Layout

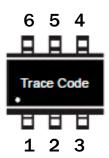


Mounting Instructions:

- 1. Use a large ground pad area near device pins 1, 2, 4, and 5 with many plated through-holes, as shown.
- 2. We recommend 1 or 2 ounces copper. Measurements for this data sheet were made on a 31mil thick FR-4 board with 1 ounce cooper on both sides.



Part Identification Marking



Ordering Information

Ordering Code	Description
SGA4263Z	7" Reel with 3000 pieces
SGA4263ZSQ	Sample bag with 25 pieces
SGA4263ZSR	7" Reel with 100 pieces
SGA4263ZPCK1	850MHz, 8V Operation PCBA with 5-piece sample bag

Mouser Electronics

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Qorvo: SGA4263Z